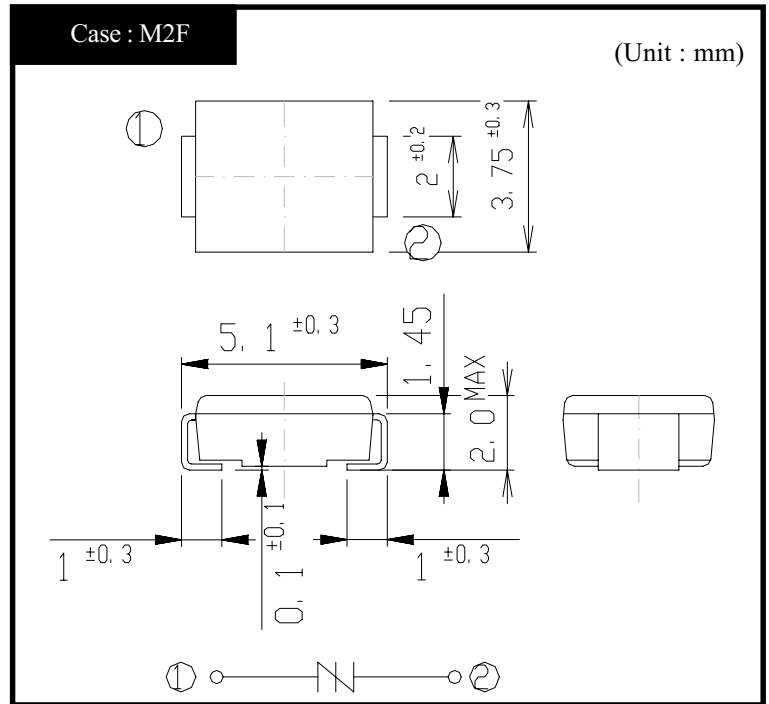


KU10S40N

OUTLINE DIMENSIONS



RATINGS

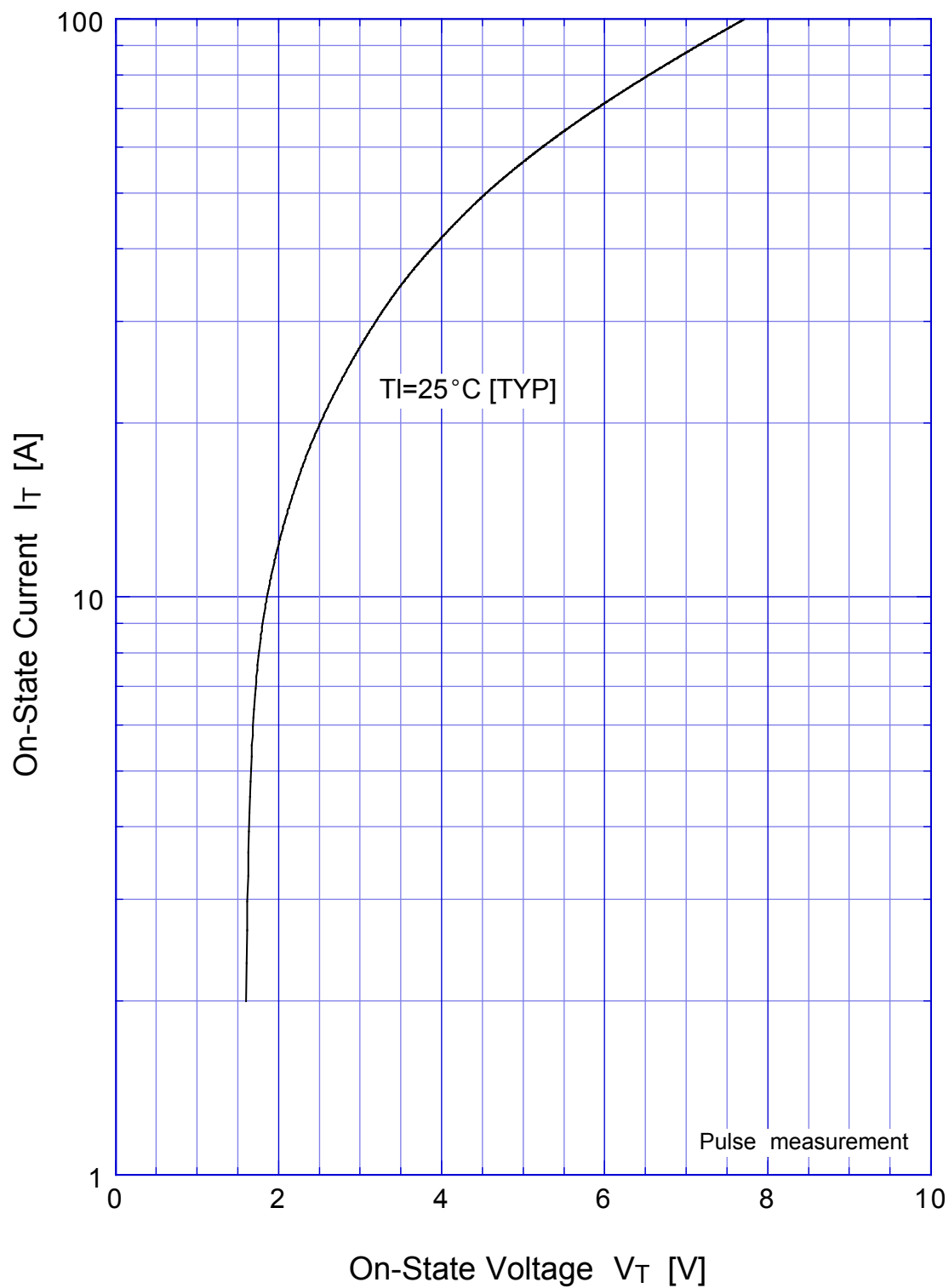
Absolute Maximum Ratings

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-40 to 125	°C
Junction Temperature	T _j		125	°C
Maximum Off-State Voltage	V _{DRM}		300	V
Surge On-State Current	I _{TSM}	Pulse-waveform 10/1000 μs, Non-repetitive	100	A

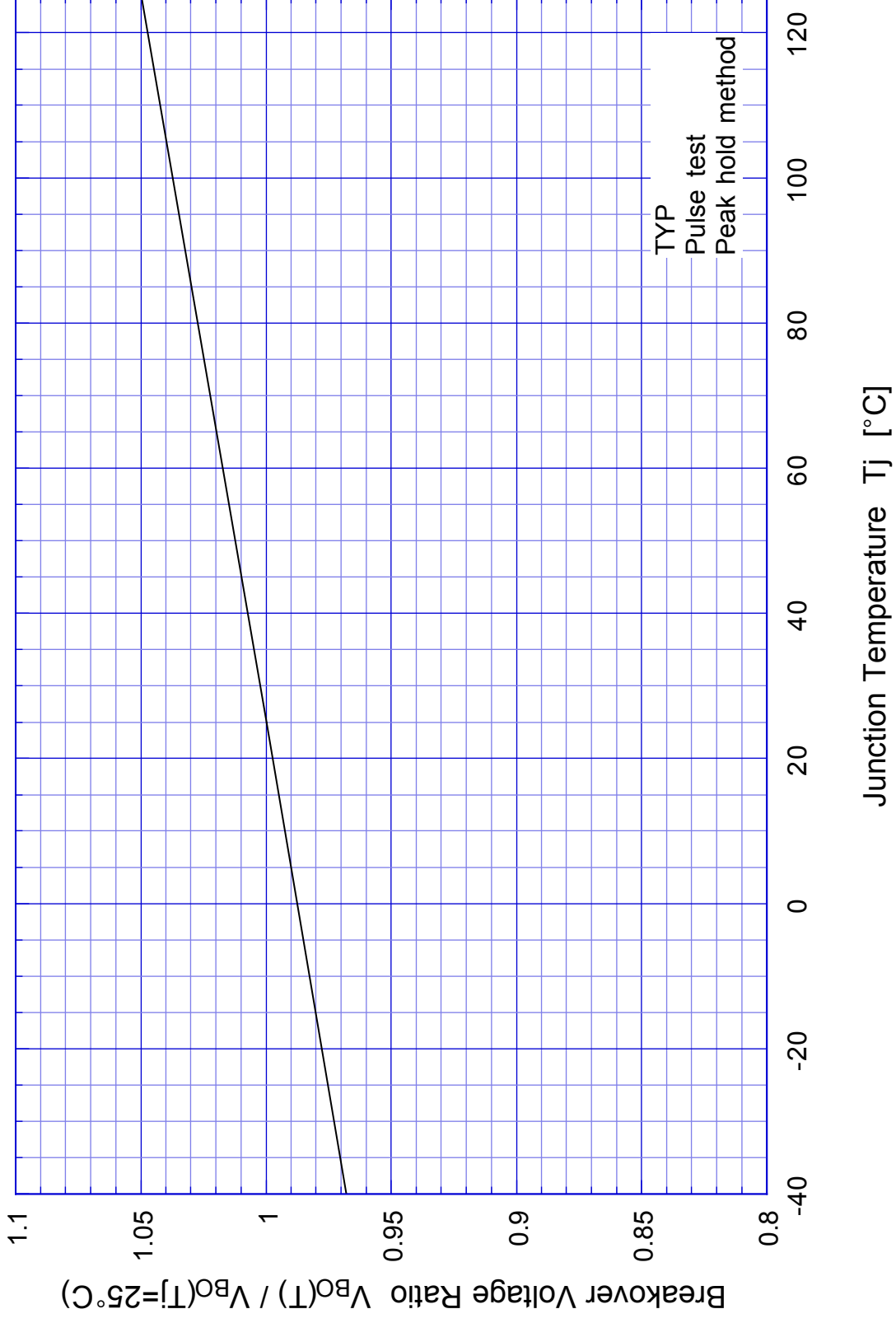
Electrical Characteristics (T_c=25°C)

Item	Symbol	Conditions	Ratings	Unit
Breakover Voltage	V _{BO}	dv/dt = 8V/ms (Peak hold)	Min 350	V
Off-State Current	I _{DRM}	V _D = V _{DRM}	Max 5.0	μA
Holding Current	I _H	Pulse measurement	Min 150(100)	mA
On-State Voltage	V _T	I _T = 2A	TYP 1.7	V
Capacitance	C _j	f = 1MHz, OSC = 1Vrms, DC = 50V	Max 90	pF
Clamping Voltage	V _{CL}	dv/dt = 100V/μs	Max 500	V

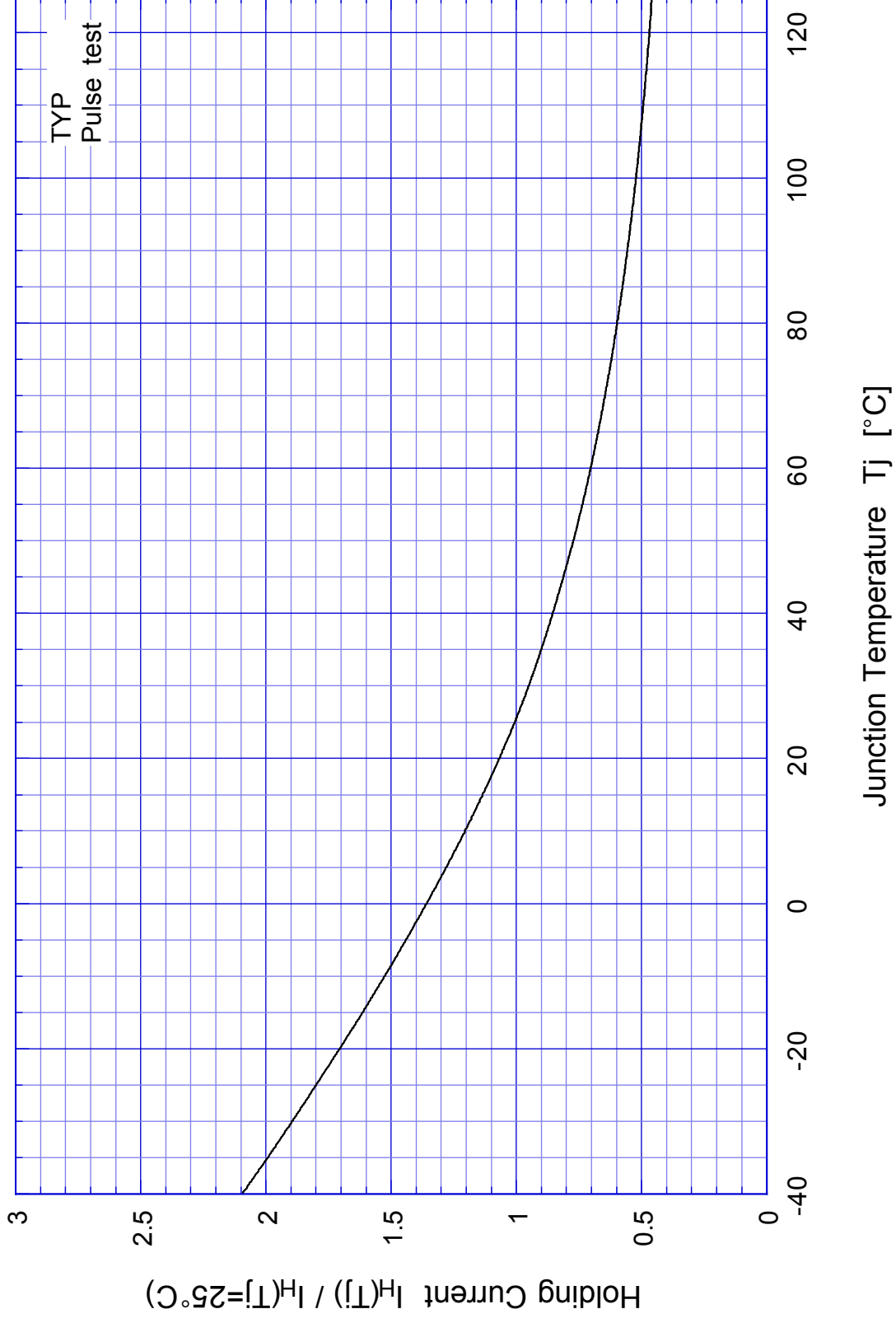
KU10S40N On-State Voltage - On-State Current



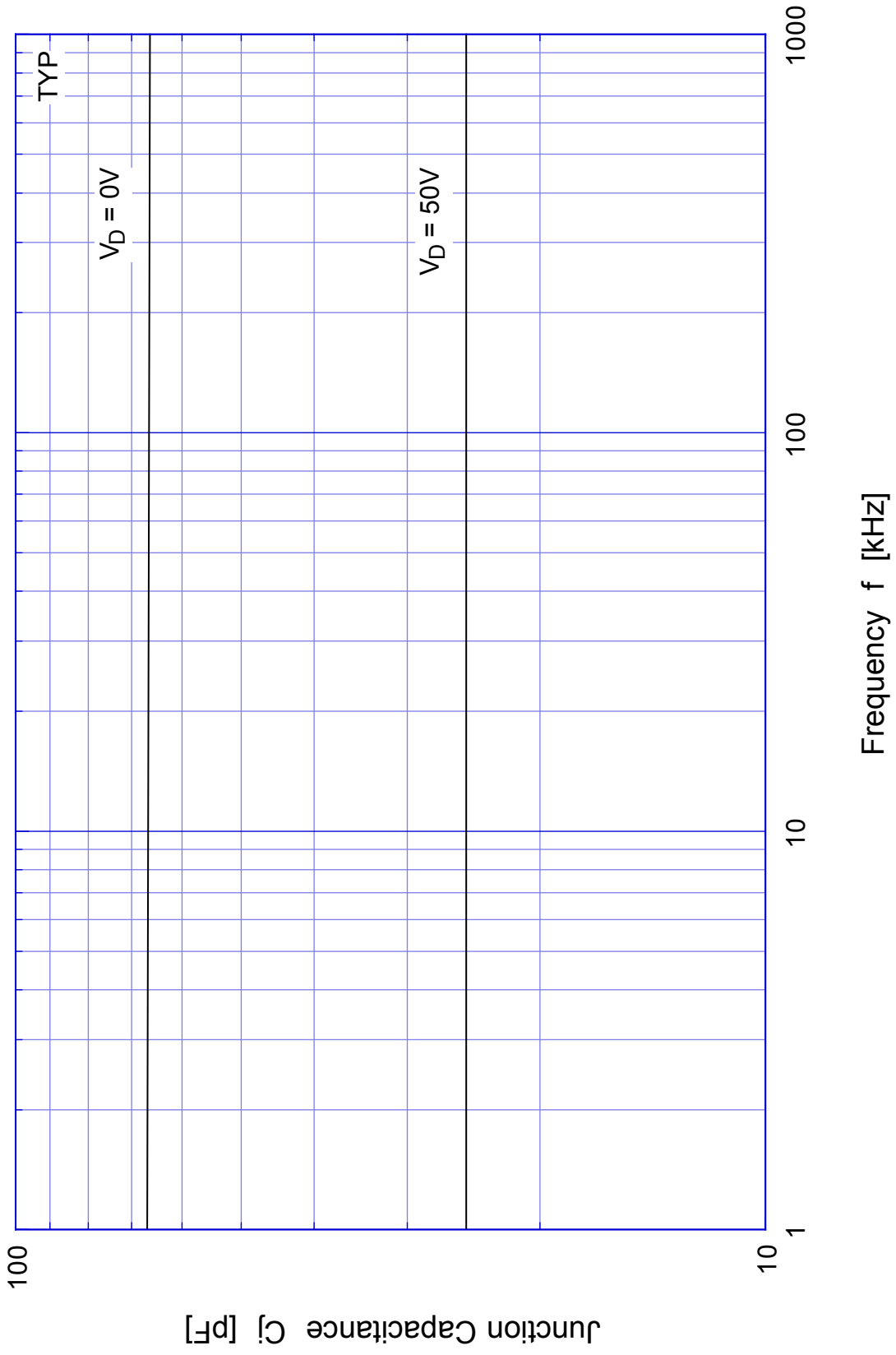
KU10S40N Breakover Voltage - Junction Temperature



KU10S40N Holding Current - Junction Temperature



KU10S40N Junction Capacitance



KU10S40N Junction Capacitance

